TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type (Darlington power transistor 4 in 1)

MP4502

High Power Switching Applications.

Hammer Drive, Pulse Motor Drive and Inductive Load Switching.

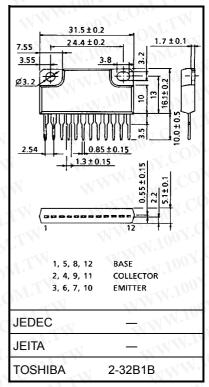
- Package with heat sink isolated to lead (SIP 12 pin)
- High collector power dissipation (4 devices operation)
 PT = 5 W (Ta = 25°C)
- High collector current: $I_{C(DC)} = 3 A \text{ (max)}$
- High DC current gain: hFE = 2000 (min) (VCE = 2 V, IC = 1.5 A)

Maximum Ratings (Ta = 25°C)

Characteristics Collector-base voltage Collector-emitter voltage Emitter-base voltage		Symbol	Rating	Unit	
		V _{CBO}	120		
		V _{CEO}	100	V	
		V _{EBO}	6	V	
Collector current	DC	Clc	3	Α	
	Pulse	I _{CP}	6		
Continuous base current		l _B	0.5	Α	
Collector power dissipa (1 device operation)	tion	Pc	3.0	W	
Collector power dissipation	Ta = 25°C	1007. P+ CO	5.0	W	
(4 devices operation)	Tc = 25°C	N.100 J.	25	•	
Isolation voltage		V _{Isol}	1000	V	
Junction temperature		Ti Ti	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Industrial Applications

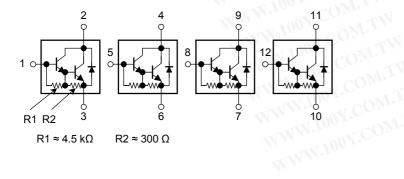
Unit: mm



Weight: 6.0 g (typ.)

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Array Configuration





Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance of channel to ambient (4 devices operation, Ta = 25°C)	ΣR _{th (j-a)}	25	°C/W
Thermal resistance of channel to case (4 devices operation, Tc = 25°C)	ΣR _{th (j-c)}	5.0	°C/W
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s)	TL	260	°C O

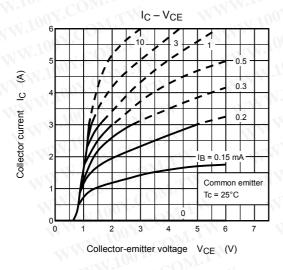
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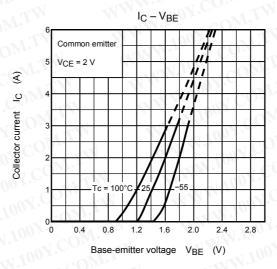
Electrical Characteristics (Ta = 25°C)

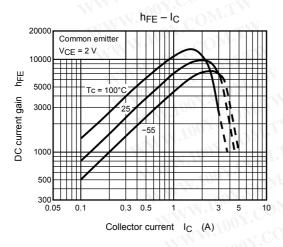
	47 0			3.0			
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	V _{CB} = 120 V, I _E = 0 A	_	VIN	10	μA
Collector cut-off current		ICEO	V _{CE} = 100 V, I _B = 0 A	_	4	10	μΑ
Emitter cut-off current		I _{EBO}	V _{EB} = 6 V, I _C = 0 A	0.5	-	2.5	mA
Collector-base breakdown voltage		V _(BR) CBO	I _C = 1 mA, I _E = 0 A	120	_		V
Collector-emitter b	reakdown voltage	V _(BR) CEO	I _C = 10 mA, I _B = 0 A	100	_		V
DC current gain		h _{FE (1)}	V _{CE} = 2 V, I _C = 1.5 A	2000	_	15000	N.10
		h _{FE (2)}	V _{CE} = 2 V, I _C = 3 A	1000	_	M.	
Saturation voltage	Collector-emitter	V _{CE (sat)}	I _C = 1.5 A, I _B = 3 mA	NEW	_	1.5	V
	Base-emitter	V _{BE (sat)}	I _C = 1.5 A, I _B = 3 mA	\T1\	_	2.0	
Transition frequency		ov. CfO	V _{CE} = 2 V, I _C = 0.5 A	_ 1	60	- <	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0 A, f = 1 MHz	O_{N_P}	30	_	pF
Switching time	Turn-on time	t _{on}	Output	CO_N	0.3	_	W
	Storage time	t _{stg}	20 μs I _{B2} Www S S V _{CC} = 30 V	ON.CO	2.0	EA A	μs
	Fall time	t _f		1007	0.4	I.EW	

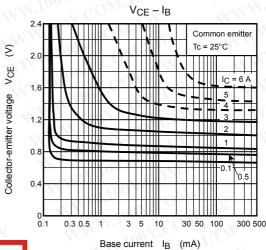
Emitter-Collector Diode Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward current	I _{FM}	V 100Y.CONT.TW	<u> </u>	1001	3	Α
Surge current	I _{FSM}	t = 1 s, 1 shot	$M_{\overline{M}_{A}}$.	_	6	Α
Forward voltage	V _F	I _F = 1 A, I _B = 0 A	_	1.2	1.8	V
Reverse recovery time	t _{rr}	I _F = 3 A, V _{BE} = -3 V, dI _F /dt = -50 A/μs	_	1.0	_	μs
Reverse recovery charge	Q _{rr}		_	5	_	μC

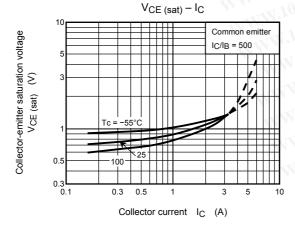


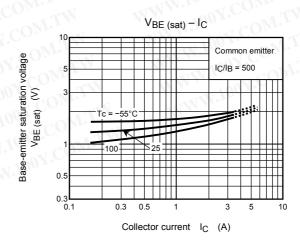




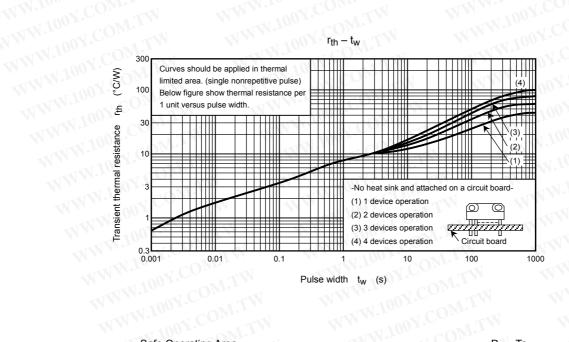


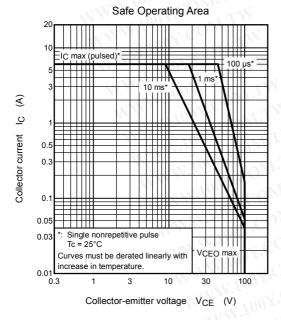
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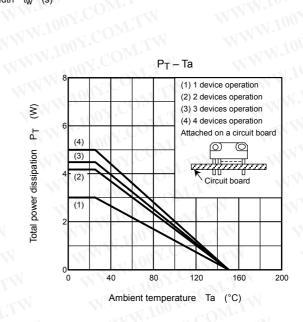




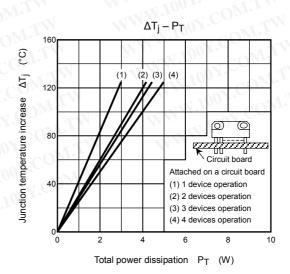
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